MOSPEC

COMPLEMENTARY SILICON PLASTIC POWER TRANSISTORS

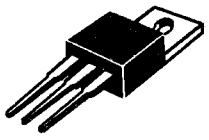
... designed for use in general purpose power amplifier and switching applications.

FEATURES:

* Collector-Emitter Sustaining Voltage -
  $V_{CEO(sus)}$= 40V(Min)- TIP41,TIP42
  60V(Min)- TIP41A,TIP42A
  80V(Min)- TIP41B,TIP42B
  100V(Min)-TIP41C,TIP42C
* Collector-Emitter Saturation Voltage- $V_{CE(sat)}$=1.5V(Max)@I_C= 6.0A
* Current Gain-Bandwidth Product f_T=3.0 MHz (Min)@ I_C=500mA

NPN	PNP
TIP41	TIP42
TIP41A	TIP42A
TIP41B	TIP42B
TIP41C	TIP42C

6 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
40 -100 VOLTS
65 WATTS



TO-220

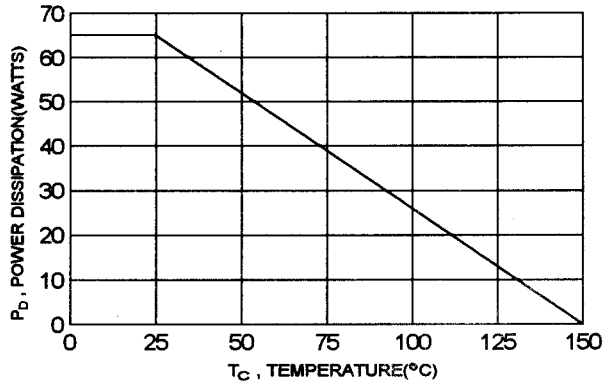
MAXIMUM RATINGS

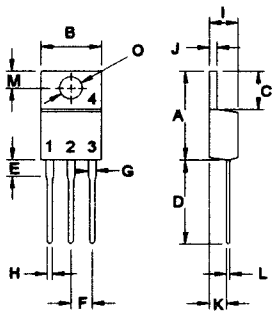
Characteristic	Symbol	TIP41 TIP42	TIP41A TIP42A	TIP41B TIP42B	TIP41C TIP42C	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	80	100	V
Collector-Base Voltage	V_{CBO}	40	60	80	100	V
Emitter-Base Voltage	V_{EBO}	5				V
Collector Current - Continuous - Peak	I_C	6 10				A
Base Current	I_B	2				A
Total Power Dissipation@T_C = 25°C Derate above 25°C	P_D	65 0.52				W W/°C
Operating and Storage Junction Temperature Range	T_J,T_{STG}	-65 to +150				°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	Rθjc	1.92	°C/W

FIGURE -1 POWER DERATING





PIN 1.BASE
2.COLLECTOR
3.EMITTER
4.COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	14.68	15.31
B	9.78	10.42
C	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.20	2.97
L	0.33	0.55
M	2.48	2.98
O	3.70	3.90

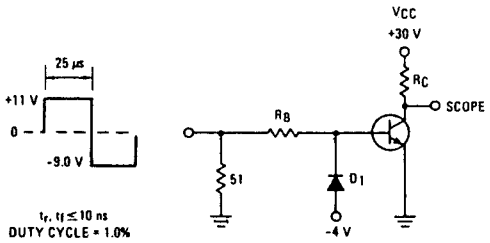
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) (I_C= 30 mA, I_B= 0)	TIP41,TIP42 TIP41A,TIP42A TIP41B,TIP42B TIP41C,TIP42C	$V_{CEO(sus)}$	40 60 80 100		V
Collector Cutoff Current (V_{CE}= 30 V, I_B= 0) (V_{CE}= 60 V, I_B= 0)	 TIP41,TIP42,TIP41A,TIP42A TIP41B,TIP42B,TIP41C,TIP42C	I_{CEO}		 0.7 0.7	mA
Collector Cutoff Current (V_{CE}= 40 V, V_{EB}= 0) (V_{CE}= 60 V, V_{EB}= 0) (V_{CE}= 80 V, V_{EB}= 0) (V_{CE}= 100 V, V_{EB}= 0)	 TIP41.TIP42 TIP41A,TIP42A TIP41B,TIP42B TIP41C,TIP42C	I_{CES}		 0.4 0.4 0.4 0.4	mA
Emitter Cutoff Current (V_{EB}= 5.0 V, I_C= 0)		I_{EBO}		1.0	mA
ON CHARACTERISTICS (1)					
DC Current Gain (I_C =0.3 A, V_{CE} = 4.0 V,) (I_C= 3.0 A, V_{CE} = 4.0 V,)		hFE	 30 15	 75	
Collector-Emitter Saturation Voltage (I_C = 6.0 A, I_B =600 mA)		$V_{CE(sat)}$		1.5	V
Base-Emitter On Voltage (I_C =6.0 A,V_{CE}= 4.0 V)		$V_{BE(On)}$		2.0	V
DYNAMIC CHARACTERISTICS					
Current Gain - Bandwidth Product (2) (I_C = 500 mA , V_{CE} = 10 V , f_{TEST} = 1 MHz)		f_T	3.0		MHz
Small Signal Current Gain (I_C = 500 mA , V_{CE} = 10 V , f = 1 kHz)		h_{fe}	20		

(1) Pulse Test: Pulse width ≦ 300 μs , Duty Cycle ≦ 2.0 %

(2) $f_T = |h_{fe}| \cdot f_{TEST}$

FIGURE 2 – SWITCHING TIME TEST CIRCUIT



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS

D_1 MUST BE FAST RECOVERY TYPE, eg:
MBD5300 USED ABOVE $I_B \approx 100$ mA
MSD6100 USED BELOW $I_B \approx 100$ mA

FIG-3 TURN-ON TIME

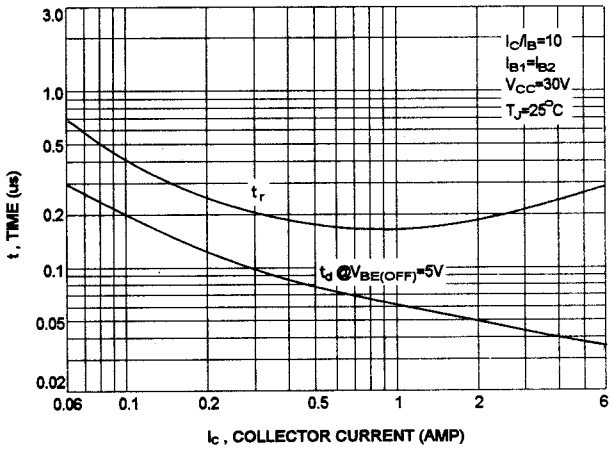


FIG-4 DC CURRENT GAIN

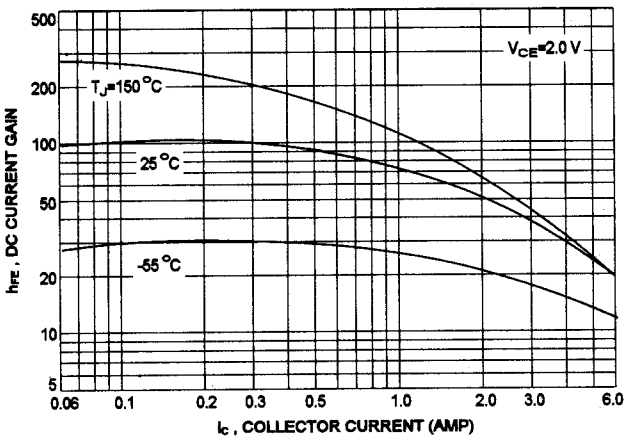


FIG-5 TURN-OFF TIME

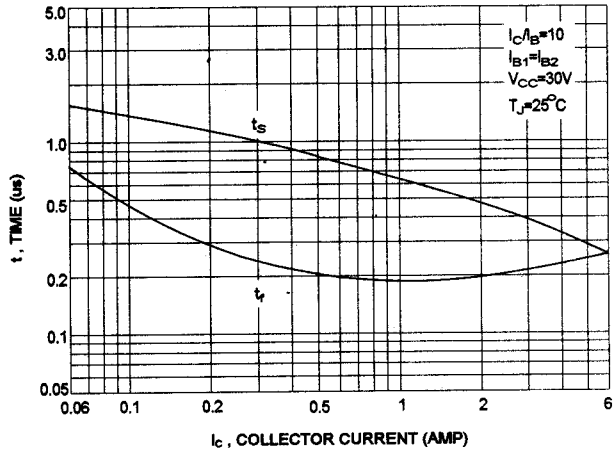
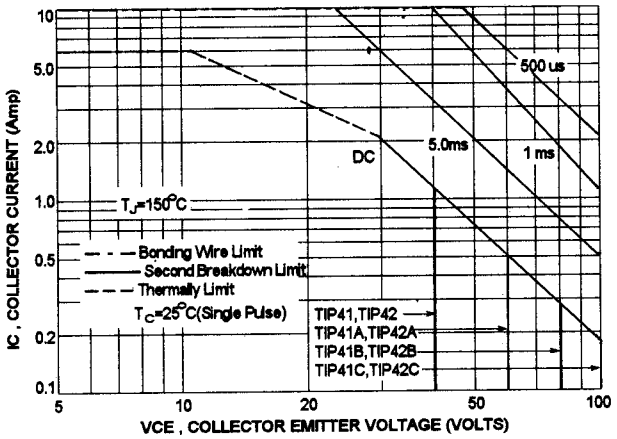


FIG-6 ACTIVE REGION SAFE OPERATING AREA



There are two limitation on the power handling ability of a transistor:average junction temperature and second breakdown safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of FIG-6 curve is base on $T_{J(PK)}$=150 °C; T_C is variable depending on power level. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 150°C$,At high case temperatures,thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

FIG-7 COLLECTOR SATURATION REGION

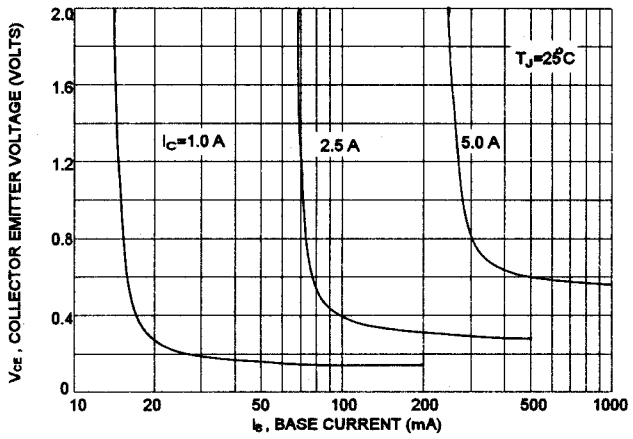


FIG-8 CAPACITANCES

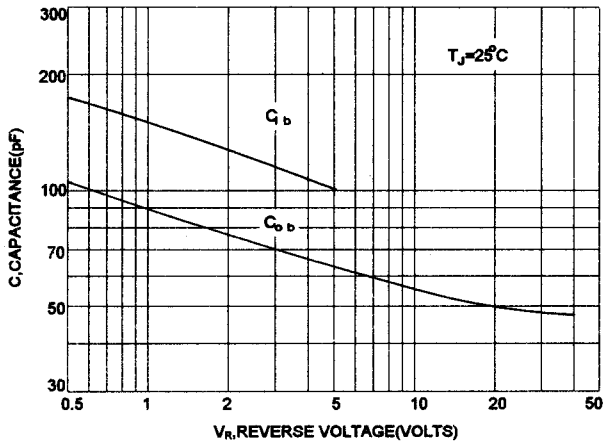


FIG-9 "ON" VOLTAGE

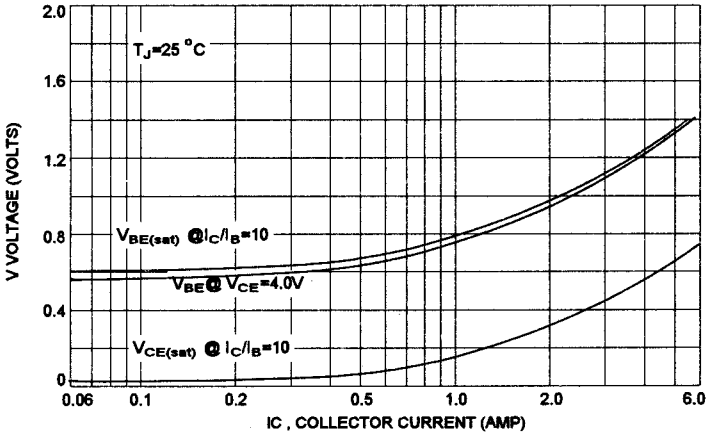


FIG-10 COLLECTOR CUT-OFF REGION